



Three-wire Serial EEPROM

2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)



Features

► Low-voltage Operation

-1.8V (Vcc = 1.8V to 5.5V)

►Three-wire Serial Interface

► Sequential Read Operation

▶2 MHz Clock Rate (5V) Compatibility

► Self-timed Write Cycle (5 ms max)

► High-reliability

- Endurance: 1 Million Write Cycles

- Data Retention: 100 Years

▶8-lead PDIP/SOP/MSOP/TSSOP, 8-pad DFN, packages

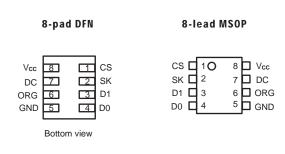
■ General Description

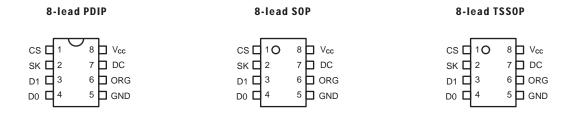
The K93C56/66 provides 2048/4096 bits of serial electrically erasable programmable read only memory (EEPROM) organized as 128/256 words of 16 bits each, when the ORG pin is connected to VCC and 256/512 words of 8 bits each when it is tied to ground. The K93C56/66 is available in space-saving 8-lead PDIP, 8-lead SOP, 8-lead TSSOP, 8-lead MSOP, and 8-pad DFN packages. The K93C56/66 is enabled through the Chip Select pin (CS), and accessed via a 3-wire serial interface consisting of Data Input (DI), Data Output (DO), and Shift Clock (SK). Upon receiving a Read instruction at DI, the address is decoded and the data is clocked out serially on the data output pin DO. The WRITE cycle is completely self-timed and no separate erase cycle is required before write. The Write cycle is only enabled when it is in the Erase/Write Enable state. When CS is brought "high" following the initiation of a write cycle, the DO pin outputs the Ready/Busy status.

■ Pin Configuration

► Table 1: Pin Configuration

Pin Name	Founctions
CS	Chip Select
SK	Serial Data Clock
DI	Serial Data Input
DO	Serial Data Output
GND	Ground
Vcc	Power Supply
ORG	Internal Organization
DC	Don't Connect



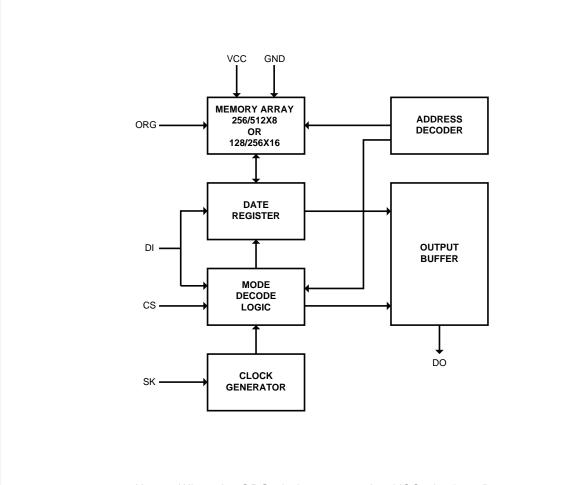


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Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)

■ Block Diagram



Notes: When the ORG pin is connected to VCC, the "x 16" organization is selected. When it is connected to ground, the "x 8" organization is selected. If the ORG pin is left unconnected and the application does not load the input beyond the capability of the internal 1 Meg ohm pullup, then the "x 16" organization is selected.

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■ Function Descriptions

The K93C56/66 is accessed via a simple and versatile three-wire serial communication interface. Device operation is controlled by seven instructions issued by the host processor. A valid instruction starts with a rising edge of CS and consists of a start bit (logic"1") followed by the appropriate op code and the desired memory address location.

► Table 2: Instruction Set for the K93C56/66

Instruction	SB	OP Code	Add	lress	Data		Comments	
IIISHUCHOII	SD	OF Code	x8	x16	x8	x16	Confinents	
READ	1	10	A8 - A0	A7 - A0			Reads data stored in memory, at specified address	
EWEN	1	00	11XXXXXXX	11XXXXXX		Write enable must precede all programming mo		
ERASE	1	11	A8 - A0	A7 - A0			Erase memory location An - A0	
WRITE	1	01	A8 - A0	A7 - A0	D7 - D0	D15 - D0	Writes memory location An - A0	
ERAL	1	00	10XXXXXXX	10XXXXXX			Erases all memory locations. Valid only at Vcc = 4.5V to 5.5V	
WRAL	1	00	01XXXXXXX	01XXXXXX	D7 - D0	D15 - D0	Writes all memory locations. Valid only at Vcc = 4.5V to 5.5V	
EWDS	1	00	00XXXXXXX	00XXXXXX			Disables all programming instructions	

Notes: The X's in the address field represent don't care values and must be clocked.

READ (**READ**): The Read (READ) instruction contains the address code for the memory location to be read. After the instruction and address are decoded, data from the selected memory location is available at the serial output pin DO. Output data changes are synchronized with the rising edges of serial clock SK. It should be noted that a dummy bit (logic "0") precedes the 8- or 16-bit data output string. The K93C56/66 supports sequential read operations. The device will automatically increment the internal address pointer and clock out the next memory location as long as Chip Select (CS) is held high .In this case ,the dummy bit (logic "0") will not be clocked out between memory locations, thus allowing for a continuous steam of data to be read.

ERASE/WRITE (EWEN): To assure data integrity, the part automatically goes into the Erase/Write Disable (EWDS) state when power is first applied. An Erase/Write Enable(EWEN) instruction must be executed first before any programming instructions can be carried out. Please note that once in the EWEN state, programming remains enabled until an EWDS instruction is executed or Vcc power is removed from the part.

ERASE (**ERASE**): The Erase (ERASE) instruction programs all bits in the specified memory location to the logical "1" state. The self-timed erase cycle starts once the ERASE instruction and address are decoded. The DO pin outputs the Ready/Busy status of the part if CS is brought high after being kept low for a minimum of 250 ns (TCS). A logic "1" at pin DO indicates that the selected memory location has been erased, and the part is ready for another instruction.

WRITE (WRITE): The Write (WRITE) instruction contains the 8 or 16 bits of data to be written into the specified memory location. The self-timed programming cycle, tWP, starts after the last bit of data is received at serial data input pin DI. The DO pin outputs the Ready/Busy status of the part if CS is brought high after being kept low for a minimum of 250 ns (TCS). A logic "0" at DO indicates that programming is still in progress. A logic "1" indicates that the memory location at the specified address has been written with the data pattern contained in the instruction and the part is ready for further instructions. A Ready/Busy status cannot be obtained if the CS is brought high after the end of the selftimed programming cycle, TWP.

ERASE ALL (ERAL): The Erase All (ERAL) instruction programs every bit in the memory array to the logic "1" state and is primarily used for testing purposes. The DO pin outputs the Ready/Busy status of the part if CS is brought high after being kept low for a minimum of 250 ns (TCS). The ERAL instruction is valid only at $V_{CC} = 5.0V \pm 10\%$.

Spring 2012 .003.







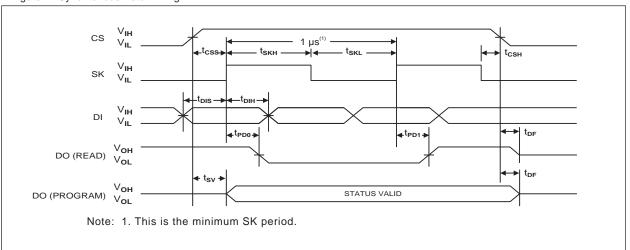
■ Function Descriptions

WRITE ALL (WRAL): The Write All (WRAL) instruction programs all memory locations with the data patterns specified in the instruction. The DO pin outputs the Ready/Busy status of the part if CS is brought high after being kept low for a minimum of 250 ns (TCS). The WRAL instruction is valid only at $Vcc = 5.0V \pm 10\%$.

ERASE/WRITE DISABLE (EWDS): To protect against accidental data disturb, the Erase/Write Disable (EWDS) instruction disables all programming modes and should be executed after all programming operations. The operation of the Read instruction is independent of both the EWEN and EWDS instructions and can be executed at any time.

■ Timing Diagrams

► Figure 1: Synchronous Data Timing



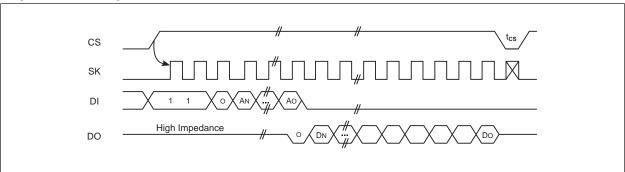
▶Table 3: Organization Key for Timing Diagram

I/O	K93C	56(2K)	K93C66(4K)		
110	X 8	X 16	X 8	X 8	
AN	A8(1)	A7(2)	A8	A7	
DN	D7	D15	D7	D15	

Note: 1. A8 is a DON'T CARE value, but the extra clock is required.

2. A7 is a DON'T CARE value, but the extra clock is required.

▶ Figure 2: READ Timing



Spring 2012 .004.

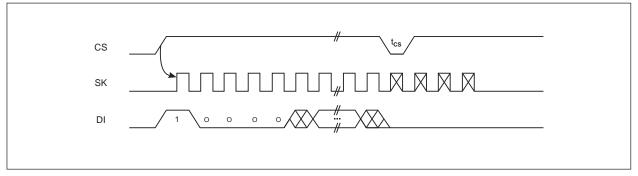


Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)

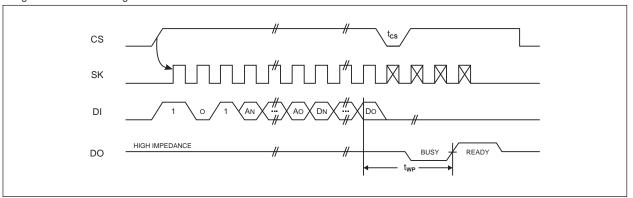
■ Timing Diagrams

▶ Figure 3: EWEN Timing CS SK DI

▶ Figure 4: EWDS Timing



▶ Figure 5: WRITE Timing

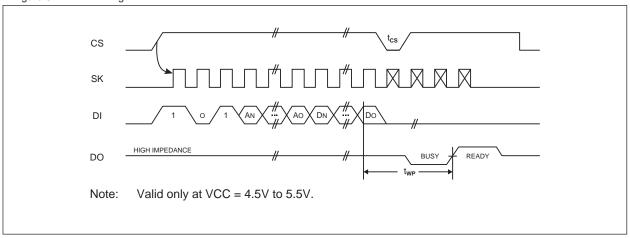


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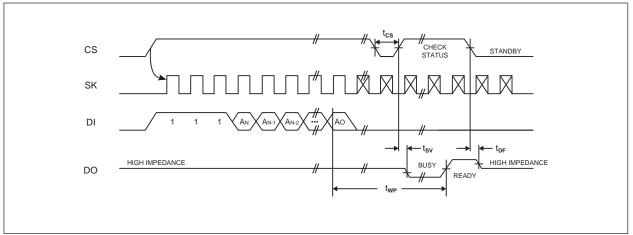
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■ Timing Diagrams

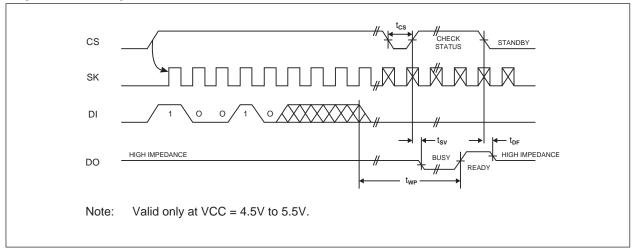
► Figure 6: WRAL Timing



▶ Figure 7: ERASE Timing



▶ Figure 8: ERAL Timing



V1.3 Spring 2012 .006.







■ Electrical Characteristics

► Absolute Maximum Ratings

DC Supply Voltage-0.3V to +6.5V

Input / Output Voltage GND-0.3V to Vcc+0.3V

Operating Ambient Temperature-40°C to +85°C

Storage Temperature-65°C to +150°C

▶ Comments

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to this device. These are stress ratings only. Functional operation of this device at these or any other conditions above those indicated in the operational sections of this specification is not implied or intended. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

■ DC Characteristics

► Applicable over recommended operating range from: T_A = -40°C to +85°C, V_{CC} = + 1.8V to + 5.5V,(unless otherwise noted)

Symbol	Parameter	Test Cond	dition	Min	Тур	Max	Units
V _{CC1}	Supply Voltage	-		1.8	-	5.5	V
V_{CC2}	Supply Voltage	-		2.7	-	5.5	V
Vcc3	Supply Voltage	-		4.5	-	5.5	V
Icc	Supply Current	Vcc = 5.0V	Read at 1.0 MHz	-	0.5	2.0	mA
ICC	Supply Current	VCC = 5.0V	Write at 1.0 MHz	-	2	3.0	mA
I _{SB1}	Standby Current	Vcc = 1.8V	CS = 0V	-	-	1.0	μΑ
I _{SB2}	Standby Current	Vcc = 2.7V	CS = 0V	-	-	1.0	μΑ
I _{SB3}	Standby Current	Vcc = 5.0V	CS = 0V	-	-	1.0	μΑ
I _{IL(1)}	Input Leakage	V _{IN} = 0V to Vcc		-	0.1	1.0	μΑ
I _{IL(2)}	Input Leakage	Vin = 0V to Vcc		-	2.0	3.0	μΑ
loL	Output Leakage	VIN = 0V	to Vcc	-	0.1	1.0	μΑ
V _{IL1(3)}	Input Low Voltage	2.7V ≤ Vc	c < 5.5V	-0.3	-	0.8	
V _{IH1(3)}	Input High Voltage	2.7 ∨ ≪ ∨ ∪	C ≈ 3.3V	2.0	-	Vcc + 0.3	V
V _{IL2(3)}	Input Low Voltage	1.8\/ < \/or	s < 2.7\/	-0.5	-	Vcc + 0.3	
$V_{\text{IH}_{2(3)}}$	Input High Voltage	1.8V ≤ Vcc ≤ 2.7V		Vcc x 0.7	-	Vcc + 0.3	V
V _{OL1}	Output Low Voltage	2.7V ≤ Vcc ≤ 5.5V	IOL = 2.1mA	-	-	0.4	V
Vон1	Output High Voltage	2.7 ∨ ≈ ∨ 00 ≈ 5.5 ∨	IOH = -0.4mA	2.4	-		V
V _{OL2}	Output Low Voltage	1.8V ≤ Vcc ≤ 2.7V	IOL = 0.15mA	-	-	0.2	V
V _{OH2}	Output High Voltage	1.0V < VCC < 2.7V	$IOH = -100\mu A$	Vcc-0.2	-	-	V

Note: VIL min and VIH max are reference only and are not tested.

■ Pin Capacitance

► Applicable over recommended operating range from TA = 25°C, f = 1.0 MHz, Vcc = +1.8V (unless otherwise noted)

	,	,	`	,
Symbol	Test Conditions	Max	Unit	Conditions
COUT	Output Capacitance (DO)	5	pF	VOUT = 0V
CIN	Input Capacitance (CS, SK, DI, ORG)	5	pF	VIN = 0V

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Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)

■ AC Characteristics

►Applicable over recommended operating range from TA = -40°C to +85°C, Vcc = + 1.8V to + 5.5V CL = 1 TTL Gate and 100pF (unless otherwise noted)

Symbol	Parameter	Test Co	ondition	Min	Тур	Max	Units
		4.5V ≤ V	/cc ≤ 5.5V	0		2	
fsк	SK Clock Frequency	2.7V ≤ V	cc ≤ 5.5V	0	-	1	MHz
		1.8V ≤ V	/cc ≤ 5.5V	0		0.25	
		4.5V ≤ V	/cc ≤ 5.5V	250			
tsкн	SK High Time	2.7V ≤ V	/cc ≤ 5.5V	250	-	-	ns
		1.8V ≤ V	/cc ≤ 5.5V	1000			
		4.5V ≤ V	/cc ≤ 5.5V	250			
tskL	SK Low Time	2.7V ≤ V	/cc ≤ 5.5V	250	-	-	ns
		1.8V ≤ V	/cc ≤ 5.5V	1000			
		4.5V ≤ V	/cc ≤ 5.5V	250			
tcs	Minimum CS Low Time	2.7V ≤ V	/cc ≤ 5.5V	250	-	-	ns
		1.8V ≤ V	cc ≤ 5.5V	1000			
			4.5V ≤ Vcc ≤ 5.5V	50			
tcss	CS Setup Time	Relative to SK	2.7V ≤ Vcc ≤ 5.5V	50	-	-	ns
			1.8V ≤ Vcc ≤ 5.5V	200			
			4.5V ≤ Vcc ≤ 5.5V	100			
tois	DI Setup Time	Relative to SK	2.7V ≤ Vcc ≤ 5.5V	100	-	-	ns
			1.8V ≤ Vcc ≤ 5.5V	400			
tсsн	CS Hold Time	Relative to SK		0	-	-	ns
			4.5V ≤ Vcc ≤ 5.5V	100			
t dih	DI Hold Time	Relative to SK	2.7V ≤ Vcc ≤ 5.5V	100	-	-	ns
			1.8V ≤ Vcc ≤ 5.5V	400			
			4.5V ≤ Vcc ≤ 5.5V			250	
t _{PD1}	Output Delay to "1"	AC Test	2.7V ≤ Vcc ≤ 5.5V	-	-	250	ns
			1.8V ≤ Vcc ≤ 5.5V			1000	
			4.5V ≤ Vcc ≤ 5.5V			250	
t _{PD0}	Output Delay to "0"	AC Test	2.7V ≤ Vcc ≤ 5.5V	-	-	250	ns
			1.8V ≤ Vcc ≤ 5.5V			1000	
			4.5V ≤ Vcc ≤ 5.5V			250	
tsv	CS to Status Valid	AC Test	2.7V ≤ Vcc ≤ 5.5V	-	-	250	ns
			1.8V ≤ Vcc ≤ 5.5V			1000	
	CS to DO in High	AC Test	4.5V ≤ Vcc ≤ 5.5V			100	
tof	Impedance	CS = VIL	2.7V ≤ Vcc ≤ 5.5V	-	-	100	ns
	impedance	OO - VIL	1.8V ≤ Vcc ≤ 5.5V			400	
twp	Write Cycle Time	-	-	-	1.5	5	ms
Endurance ⁽¹⁾	5.0V, 25°C		-	1M	-	-	Write Cycle

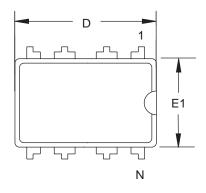
Note: 1. This parameter is characterized and is not 100% tested.

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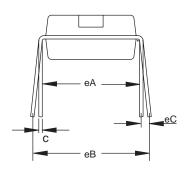
Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)



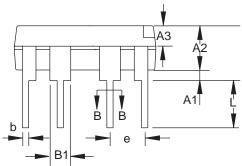
■ 8-lead PDIP package diagram



Top View

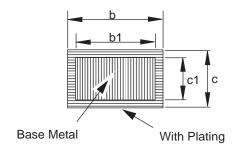


End View



Side View





Section B-B

COMMON DIMENSIONS

(Unit of Measure = mm)

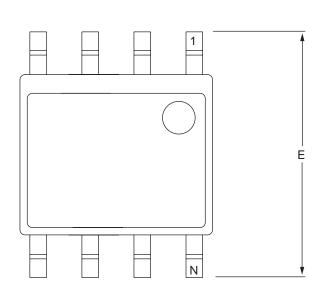
SYMBOL	MIN	MAX		
Α	3.60	4.00		
A1	0.51	-		
A2	3.10	3.50		
A3	1.50	1.70		
b	0.44	0.53		
b1	0.43	0.48		
В	1.52 BSC			
С	0.25	0.31		
c1	0.24	0.26		
D	9.05	9.45		
E1	6.15	6.55		
е	2.54 BSC			
eA	7.62 BSC			
eB	7.62	9.50		
eC	0	0.94		
L	3.00	-		

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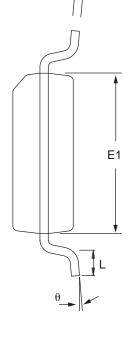
Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)



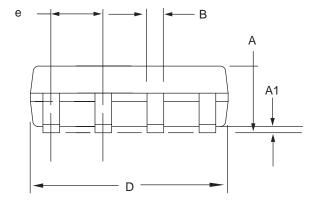
■ 8-lead SOP package diagram



Top View



End View



Side View

COMMON DIMENSIONS

(Unit of Measure = mm)

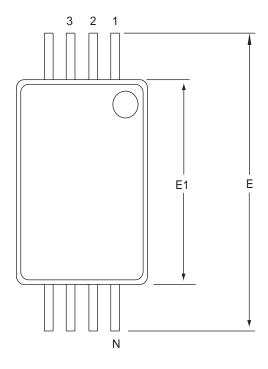
SYMBOL	MIN	MAX
А	1.35	1.75
A1	0.10	0.25
b	0.31	0.51
С	0.17	0.25
D	4.70	5.10
E1	3.80	4.00
Е	5.79	6.20
е	1.27	BSC
L	0.40	1.27
θ	0°	8°

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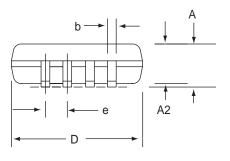
Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)



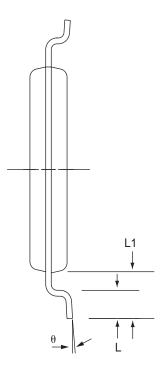
■ 8-lead TSSOP package diagram



Top View



Side View



End View

COMMON DIMENSIONS

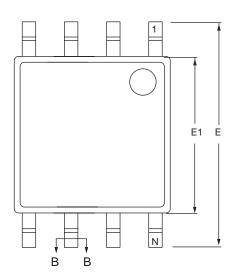
(Unit of Measure = mm)

(=						
SYMBOL	MIN	MAX				
D	2.80	3.20				
E	6.20	6.60				
E1	4.20	4.60				
А	A – 1.20					
A2	A2 0.80 1.15					
b	0.19	0.30				
е	0.65	BSC				
L	0.45	0.75				
L1	1.00 BSC					
θ	0°	8°				

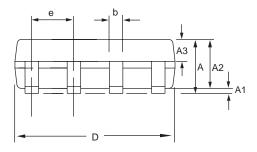
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Three-wire Serial EEPROM 2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)

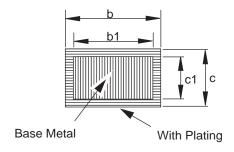
■ 8-lead MSOP package diagram



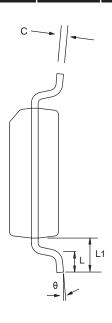
Top View



Side View



Section B-B



End View

COMMON DIMENSIONS

(Unit of Measure = mm)

SYMBOL	MIN	MAX		
А	-	1.10		
A1	0.05	0.15		
A2	0.75	0.95		
A3	0.30	0.40		
b	0.29	0.38		
b1	0.28	0.33		
С	0.15 0.20			
c1	0.14	0.16		
D	2.90	3.10		
Е	4.70	5.10		
E1	2.90	3.10		
е	0.65 BSC			
L	0.40	0.70		
L1	0.95 BSC			
θ	0°	8°		

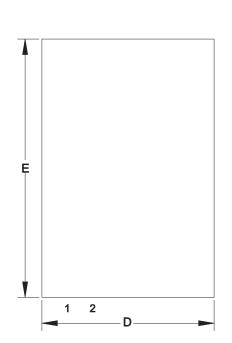
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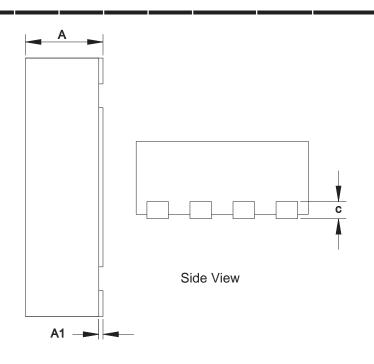






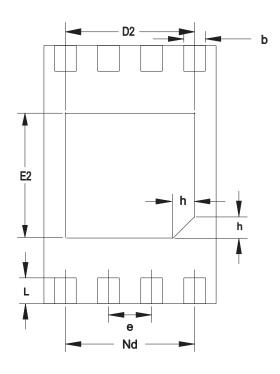
■ 8-pad DFN package diagram





Top View

End View



Bottom View

COMMON DIMENSIONS (Unit of Measure = mm)

SYMBOL	MIN	MAX	
Α	0.70	0.80	
A1	-	0.05	
b	0.18	0.30	
С	0.18	0.25	
D	1.90	2.10	
D2	1.50 REF		
е	0.50	BSC	
Nd	1.50	BSC	
E	2.90	3.10	
E2	1.60 BSC		
L	0.30	0.50	
h	0.20	0.30	

V1.3 Spring 2012 .013.







■ Ordering Information

Product Name: XXX Κ 93 Part Number: X X X XΧ Κ 93 XXX 5 8 (version) 2 4 6 7 3

1.Prefix

93: Three-wire (SPI) Interface 3.EEPROM Density

C56 = 2K bitsC66 = 4K bits

4.Package Type

D = PDIP S = SOPT = TSSOPM = MSOPN = DFN

5.Temperature Range

 $I = Industry (-40^{\circ}C to +85^{\circ}C)$ 6.Pack Type T = Tube R = Tape & Reel

7.Plating Technology

Blank = Standard SnPb plating G = RoHS compliant

S = Green, level 1 X = Green, level 3

8. Operating Voltage

A = 1.8 to 5.5 V

■ Available package types

Model	PDIP	SOP	TSSOP	MSOP	DFN
K93C56	\checkmark	\checkmark	\checkmark	\checkmark	V
K93C66	V	\checkmark	V	\checkmark	V

■ Product Datasheet Change Notice

Datasheet Revision History		
Version	Content	Date
1.0	Initial version	Dec., 2008
1.1	Package type update	Jan., 2011
1.2	Ordering information update	May, 2011
1.3	Ordering information update	Jan., 2012

V1.3 Spring 2012 .014.

Three-wire Serial EEPROM

2K bits (256 X 8 or 128 X 16) / 4K bits (512 X 8 or 256 X 16)



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K93C Series (SPI Bus) Serial EEPROM Data Sheet, Revision 1.3

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